NSN 5962-01-203-8640

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View Online at https://aerobasegroup.com/nsn/5962-01-203-8640

Body Length:
0.840 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
0.185 inches
Maximum Power Dissipation Rating:
794.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
3-state output and bipolar and programmed and schottky and w/active pull-up
Inclosure Material:
Ceramic or glass or metal
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Case Outline Source And Designator:
D-2 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
85.00 nanoseconds propagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to low le
output
Memory Device Type:
Prom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
16 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:

Yes - demil/mli

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